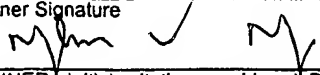


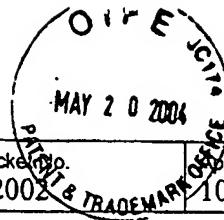
Substitute Form PTO-1449 (Modified)  <b>Information Disclosure Statement          by Applicant</b> (Use several sheets if necessary)  (37 CFR §1.98(b))	U.S. Department of Commerce Patent and Trademark Office	Attorney's Docket No. 12732-092002	Application No. 10/718,584
	Applicant Shunpei Yamazaki et al.		
	Filing Date November 24, 2003	Group Art Unit 2811	

U.S. Patent Documents							
Examiner Initial	Desig. ID	Document Number	Publication Date	Patentee	Class	Subclass	Filing Date If Appropriate
W	AA	5,990,998	11/23/1999	Park et al.			04/10/1997
	AB						
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Foreign Patent Documents or Published Foreign Patent Applications								
Examiner Initial	Desig. ID	Document Number	Publication Date	Country or Patent Office	Class	Subclass	Translation	
							Yes	No
	AL							
	AM							
	AN							
	AO							
	AP							

Other Documents (include Author, Title, Date, and Place of Publication)		
Examiner Initial	Desig. ID	Document
	AQ	
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Examiner Signature 	Date Considered 5-25-05
EXAMINER: Initials citation considered. Draw line through citation if not in conformance and not considered. Include copy of this form with next communication to applicant.	

Sheet 1 of 1Substitute Form PTO-1449  
(Modified)U.S. Department of Commerce  
Patent and Trademark OfficeAttorney's Docket No.  
12732-092002Application No.  
10/718,584**Information Disclosure Statement  
by Applicant**

(Use several sheets if necessary)

(37 CFR §1.98(b))

Applicant  
Shunpei Yamazaki et al.Filing Date  
November 24, 2003Group Art Unit  
2811**U.S. Patent Documents**

Examiner Initial	Desig. ID	Document Number	Publication Date	Patentee	Class	Subclass	Filing Date If Appropriate
	AA						
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**Foreign Patent Documents or Published Foreign Patent Applications**

Examiner Initial	Desig. ID	Document Number	Publication Date	Country or Patent Office	Class	Subclass	Translation	
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nm	AL	0 082 012 A2	06/22/1983	EUROPE	<u>  </u>	<u>  </u>	In English	
	AM							
	AN							
	AO							
	AP							

**Other Documents (include Author, Title, Date, and Place of Publication)**

Examiner Initial	Desig. ID	Document
nm	AQ	Australian Patent Office Search Report (Application No. SG 200200805-0), 8 pages
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Examiner Signature

Date Considered

5-25-05

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Substitute Disclosure Form (PTO-1449)

Substitute Form PTO-1449 (Modified)  <b>Information Disclosure Statement by Applicant</b> (Use several sheets if necessary)  (37 CFR §1.98(b))	U.S. Department of Commerce Patent and Trademark Office	Attorney's Docket No. 12732-092002	Application No. New Divisional
	Applicant Shunpei Yamazaki et al.		
	Filing Date November 24, 2003	Group Art Unit Unknown	

U.S. Patent Documents							
Examiner Initial	Desig. ID	Document Number	Publication Date	Patentee	Class	Subclass	Filing Date If Appropriate
NW	AA	US 2002/0110941 A1	08/15/2002	Yamazaki et al.			01/26/2001
	AB	US 2002/0070382 A1	06/13/2002	Yamazaki et al.			12/11/2001
	AC	US 2001/0055841 A1	12/27/2001	Yamazaki et al.			04/12/2001
	AD	US 2001/0052950 A1	12/20/2001	Yamazaki et al.			03/16/2001
	AE	US 2001/0049197 A1	12/06/2001	Yamazaki et al.			06/04/2001
	AF	US 2001/0030322 A1	10/18/2001	Yamazaki et al.			02/02/2001
	AG	US 2002/0017685 A1	02/14/2002	Kasahara et al.			05/03/2001
	AH	US 2002/0016028 A1	02/07/2002	Arao et al.			06/05/2001
	AI	US 2002/0013022 A1	01/31/2002	Yamazaki et al.			05/09/2001
	AJ	US 2002/0006705 A1	01/17/2002	Suzawa et al.			05/10/2001
	AK	6,031,290	02/29/2000	Miyazaki et al.			03/13/1998
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Examiner Initial	Desig. ID	Document Number	Publication Date	Country or Patent Office	Class	Subclass	Translation	
							Yes	No
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Sheet 1 of 1

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Examiner Initial	Desig. ID	Document Number	Publication Date	Patentee	Class	Subclass	Filing Date If Appropriate
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<i>W</i>	AB	6,399,454 B1	06/04/2002	Yamazaki	1	1	07/13/1998
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	AB	3,791,883	02/12/1974	Takei et al.			—
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	AS	5,352,291	10/04/1994	Zhang et al.			—
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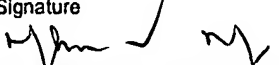
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	Applicant Shunpei Yamazaki et al.		
	Filing Date November 24, 2003	Group Art Unit 2811	

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nr	ABB	5,773,327	06/30/1998	Yamazaki et al.			
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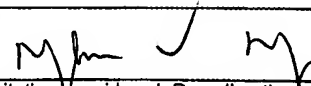
Foreign Patent Documents or Published Foreign Patent Applications								
Examiner Initial	Desig. ID	Document Number	Publication Date	Country or Patent Office	Class	Subclass	Translation	
							Yes	No
nr	AII	JP 04-011722	01/16/1992	Japan			Full	
	AJJ	JP 06-013610	01/21/1994	Japan			Abs	
	AKK	JP 06-267978	09/22/1994	Japan			Abs	
	ALL	JP 56-024925	03/10/1981	Japan			Abs	
nr	AMM	JP 60-105216	06/10/1985	Japan			Abs	

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nr	ANN	S. Caune et al.; "Combined CW Laser and Furnace Annealing of Amorphous Si and Ge in Contact with some Metals"; <u>Applied Surface Science</u> , vol. 36, pp. 597-604 (1989)
	AOO	B.C. Ahn et al.; "Batch-Processing of High-Performance Amorphous-Silicon/Silicon-Nitride Thin-Film Transistors" <u>IEEE Display Research Conference</u> , pp. 85-88 (1991)
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	AQQ	L. Hultman et al.; "Crystallization of Amorphous Silicon During Thin-film Gold Reaction"; <u>J. Appl. Phys.</u> , vol. 62, no. 9; pp. 3647-3655 (November 1987)
nr	ARR	Yunosuke Kawazu et al.; "Low-Temperature Crystallization of Hydrogenated Amorphous Silicon Induced by Nickel Silicide Formation"; <u>Japanese Journal of Applied Physics</u> , vol. 29, no. 12; pp. 2698-2704 (1990)

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<b>Information Disclosure Statement by Applicant</b> (Use several sheets if necessary)		Applicant Shunpei Yamazaki et al.	
		Filing Date November 24, 2003	Group Art Unit 2811
(37 CFR §1.98(b))			

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